

PTO/SB/08a Substitute for Form 1449A/PTO			Application Number	10/530,848	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Filing Date	April 8, 2005	
			First Named Inventor	ARMIN ABERLE	
			Art Unit	Not Yet Assigned	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	2	Attorney Docket	85267

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ²			
/J.S./		US-5,275,851 A	01/04/1994	Fonash et al.	
/J.S./		US-5,344,796 A	09/06/1994	Shin et al.	
/J.S./		US-6,097,037 A	08/01/2000	Joo et al.	
/J.S./		US-6,248,675 B1	06/19/2001	Xiang et al.	
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FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵			
/J.S./		EP 1 271 620 A1	01/02/2003	Hyoung June Kim	
/J.S./		JP 2002261305	09/13/2002	Toyota Central Res. & Dev. Lab Inc.	

Examiner Signature	/Julia Slutsker/	Date Considered	05/16/2008
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PTO/SB/08b Substitute for Form 1449B/PTO		Application Number		10/530,848	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Filing Date		April 8, 2005	
		First Named Inventor		ARMIN ABERLE	
		Art Unit		Not Yet Assigned	
		Examiner Name		Not Yet Assigned	
Sheet	2	of	2	Attorney Docket	85267

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²		
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